LSIC2SD120D10 Series



Circuit Diagram TO-263-2L



Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

• Extremely fast,

temperature-independent switching behavior

• Dramatically reduced

compared to Si bipolar

switching losses

diodes

• Solar inverters

• Industrial motor drives

• EV charging stations

HF RoHS 🖗

Features

- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability

Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies

Environmental

- Littelfuse "RoHS" logo = RoHS **RoHS** conform
- Littelfuse "HF" logo = HF Halogen Free
- Littelfuse "Pb-free" logo = Po Pb-free lead plating

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	-	1200	V	
DC Blocking Voltage	V _R	T _i = 25 °C	1200	V	
		T _c = 25 °C	28		
Continuous Forward Current	I _F	T _c = 125 °C	15	А	
		T _c = 151 °C	10		
Non-Repetitive Forward Surge Current	I _{FSM}	$T_c = 25 \text{ °C}, T_p = 10 \text{ ms}, \text{ Half sine pulse}$	80	А	
Power Dissipation	D	T _c = 25 °C	136	W	
rower dissipation	P _{Tot}	T _c = 110 °C	59		
Operating Junction Temperature	TJ	-	-55 to 175	°C	
Storage Temperature	T _{stg}	-	-55 to 150	°C	
Soldering Temperature (reflow MSL1)	T _{sold}	-	260	°C	

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Electrical Characteristics

Characteristics Symbo			Value			
	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward Voltage	N	I _F = 10 A, T _J = 25 °C	-	1.5	1.8	V
	V _F	I _F = 10 A, T _J = 175 °C	-	2.2		
Reverse Current	1	$V_{_{ m R}} = 1200 \text{ V}$, $T_{_{ m J}} = 25 \ ^{\circ}\text{C}$	-	<1	100	μA
	R	V _R = 1200 V , T _J = 175 °C	-	10		
Total Capacitance C		V _R = 1 V, f = 1 MHz	-	582		pF
	С	V _R = 400 V, f = 1 MHz	-	53		
		$V_{_{\rm R}} = 800 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	40		
otal Capacitive Charge	O _c	$V_{R} = 800 \text{ V, } Q_{c} = \int C(V) dV$	-	57		nC

Footnote: $T_1 = +25 \text{ °C}$ unless otherwise specified

Thermal Characteristics						
Characteristics Symbol		Symbol Conditions	Value			
	Symbol		Min.	Тур.	Max.	Unit
Thermal Resistance	R _{euc}	-	-	1.1		°C/W

Figure 1: Typical Foward Characteristics



Figure 2: Typical Reverse Characteristics



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GEN2 SiC Schottky Diode LSIC2SD120D10, 1200 V, 10 A, TO-263-2L

Figure 3: Power Derating



Figure 5: Capacitance vs. Reverse Voltage



Figure 7: Stored Energy vs. Reverse Voltage



Figure 4: Current Derating



Figure 6: Capacitive Charge vs. Reverse Voltage



Figure 8: Transient Thermal Impedance



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Dimensions-Package TO-263-2L



O maked	Millimeters				
Symbol	Min	Nom	Мах		
А	4.30	4.50	4.70		
A1	0.00	-	0.25		
b	0.70	0.80	0.90		
b1	1.17	1.27	1.37		
С	0.46	0.50	0.60		
c1	1.25	1.30	1.40		
D	9.00	9.20	9.40		
D1	6.50	6.70	6.90		
E	9.80	10.00	10.20		
E1	7.80	8.00	8.20		
E2	9.70	9.90	10.10		
е	5.08 BSC				
н	15.00	15.30	15.60		
L	2.00	2.30	2.60		
L1	1.00	1.20	1.40		
L2	0.254 BSC				

Part Numbering and Marking System



=	SiC	Diode
	010	Diouc

- = Gen2
- = Schottky Diode = Voltage Rating (1200 V)
- = TO-263 Package (2 Lead)
- = Current Rating (10 A)
- YY = Year WW = Week F = Special Code
- ZZZZZZ-ZZ = Lot Number

Packing Option

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD120D10	SIC2SD120D10	Tape and Reel	800

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TO-263 Carrier Reel Specifications



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